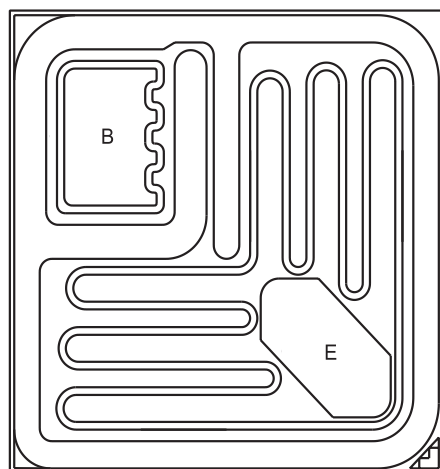


**PROCESS DETAILS**

|                          |                      |
|--------------------------|----------------------|
| Process                  | EPITAXIAL BASE       |
| Die Size                 | 111 X 111 MILS       |
| Die Thickness            | 10 MILS              |
| Base Bonding Pad Area    | 20 X 30 MILS         |
| Emitter Bonding Pad Area | 20 X 26 MILS         |
| Top Side Metalization    | Al - 30,000Å         |
| Back Side Metalization   | Au/Cr/Ni/Au - 6,000Å |

**GEOMETRY****BACKSIDE COLLECTOR**

R1

**GROSS DIE PER 5 INCH WAFER**

910

**PRINCIPAL DEVICE TYPES**

2N6040

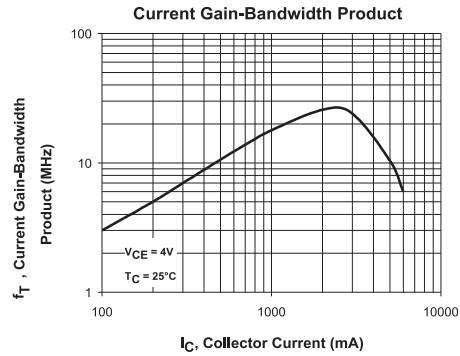
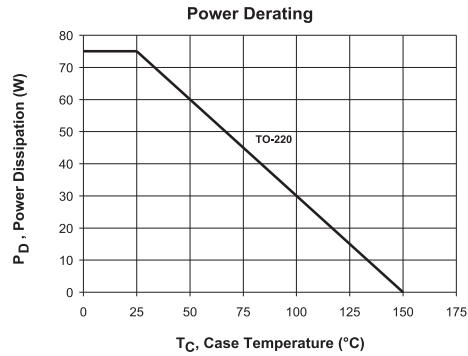
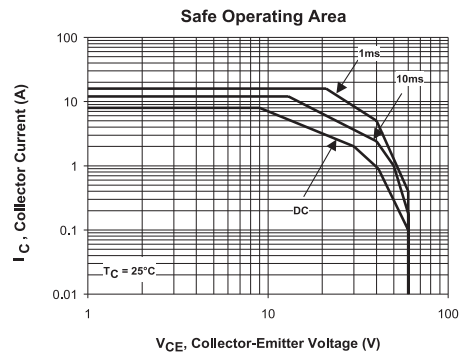
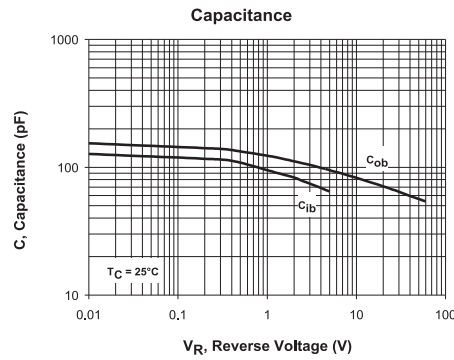
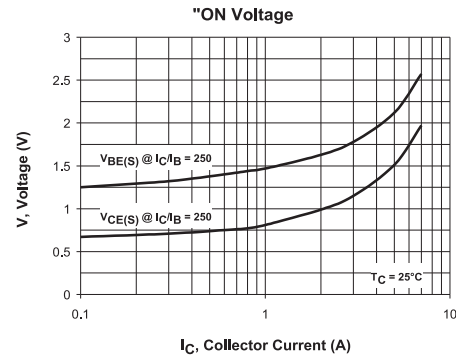
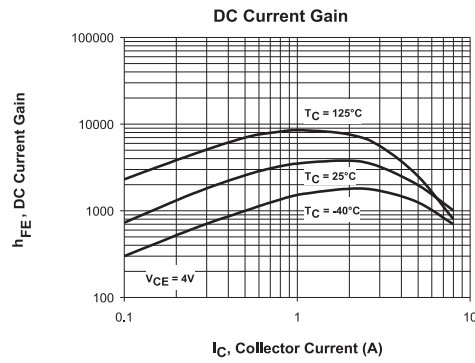
2N6041

2N6042

2N6299

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